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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Active
Core Processor	ARM® Cortex®-A9
Number of Cores/Bus Width	4 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	Multimedia; NEON™ SIMD
RAM Controllers	LPDDR2, DDR3L, DDR3
Graphics Acceleration	Yes
Display & Interface Controllers	HDMI, Keypad, LCD, LVDS, MIPI/DSI, Parallel
Ethernet	10/100/1000Mbps (1)
SATA	SATA 3Gbps (1)
USB	USB 2.0 + PHY (3), USB 2.0 OTG + PHY (1)
Voltage - I/O	1.8V, 2.5V, 2.8V, 3.3V
Operating Temperature	-20°C ~ 105°C (TJ)
Security Features	ARM TZ, A-HAB, CAAM, CSU, SJC, SNVS
Package / Case	624-LFBGA, FCBGA
Supplier Device Package	624-FCPBGA (21x21)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mcimx6qp5eym1ab

4.1.2 Thermal Resistance

NOTE

Per JEDEC JESD51-2, the intent of thermal resistance measurements is solely for a thermal performance comparison of one package to another in a standardized environment. This methodology is not meant to and will not predict the performance of a package in an application-specific environment.

4.1.2.1 FCPBGA Package Thermal Resistance

Table 5 provides the FCPBGA package thermal resistance data for the *non-lidded* package type.

Table 5. FCPBGA Package Thermal Resistance Data (Non-Lidded)

Thermal Parameter	Test Conditions	Symbol	Value	Unit
Junction to Ambient[1]	Single-layer board (1s); natural convection[2]	$R_{\theta JA}$	31	°C/W
	Four-layer board (2s2p); natural convection[2]	$R_{\theta JA}$	22	°C/W
Junction to Ambient[1]	Single-layer board (1s); air flow 200 ft/min[3]	$R_{\theta JMA}$	24	°C/W
	Four-layer board (2s2p); air flow 200 ft/min[3]	$R_{\theta JMA}$	18	°C/W
Junction to Board[1,4]	—	$R_{\theta JB}$	12	°C/W
Junction to Case (top)[1,5]	—	$R_{\theta JCtop}$	<0.1	°C/W

[1] Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.

[2] Per JEDEC JESD51-3 with the single layer board horizontal. Thermal test board meets JEDEC specification for the specified package.

[3] Per JEDEC JESD51-6 with the board horizontal.

[4] Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.

[5] Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1). The cold plate temperature is used for the case temperature. Reported value includes the thermal resistance of the interface layer.

4.1.3 Operating Ranges

Table 6 provides the operating ranges of the i.MX 6DualPlus/6QuadPlus processors.

Table 6. Operating Ranges

Parameter Description	Symbol	Min	Typ	Max[1]	Unit	Comment[2]
Run mode: LDO enabled	VDD_ARM_IN VDD_ARM23_IN[3]	1.4[4]	—	1.5	V	LDO Output Set Point (VDD_ARM_CAP[5]) of 1.275 V minimum for operation up to 1200 MHz. **Only supported in LDO enabled mode.**
		1.35[4]	—	1.5	V	LDO Output Set Point (VDD_ARM_CAP[5]) of 1.225 V minimum for operation up to 996 MHz.
		1.275[4]	—	1.5	V	LDO Output Set Point (VDD_ARM_CAP[5]) of 1.150 V minimum for operation up to 792 MHz.
		1.05[4]	—	1.5	V	LDO Output Set Point (VDD_ARM_CAP[5]) of 0.925 V minimum for operation up to 396 MHz.
	VDD_SOC_IN[6]	1.35[4]	—	1.5	V	264 MHz < VPU ≤ 352 MHz; VDDSOC and VDDPU LDO outputs (VDD_SOC_CAP and VDD_PU_CAP) require 1.275 V minimum.
		1.275[4,7]	—	1.5	V	VPU ≤ 264 MHz; VDDSOC and VDDPU LDO outputs (VDD_SOC_CAP and VDD_PU_CAP) require 1.15 V minimum.
Run mode: LDO bypassed[8]	VDD_ARM_IN VDD_ARM23_IN[3]	1.225	—	1.3	V	LDO bypassed for operation up to 996 MHz.
		1.150	—	1.3	V	LDO bypassed for operation up to 792 MHz.
		0.925	—	1.3	V	LDO bypassed for operation up to 396 MHz.
	VDD_SOC_IN[6]	1.225	—	1.3	V	264 MHz < VPU ≤ 352 MHz
		1.15	—	1.3	V	VPU ≤ 264 MHz
Standby/DSM mode	VDD_ARM_IN VDD_ARM23_IN[3]	0.9	—	1.3	V	See Table 9, "Stop Mode Current and Power Consumption," on page 28.
	VDD_SOC_IN	1.05	—	1.3	V	
VDD_HIGH internal regulator	VDD_HIGH_IN[9]	2.7	—	3.6	V	Must match the range of voltages that the rechargeable backup battery supports.
Backup battery supply range	VDD_SNVS_IN[9]	2.8	—	3.6	V	Should be supplied from the same supply as VDD_HIGH_IN, if the system does not require keeping real time and other data on OFF state.
USB supply voltages	USB_OTG_VBUS	4.4	—	5.25	V	—
	USB_H1_VBUS	4.4	—	5.25	V	—
DDR I/O supply	NVCC_DRAM	1.14	1.2	1.3	V	LPDDR2
		1.425	1.5	1.575	V	DDR3
		1.283	1.35	1.45	V	DDR3L
Supply for RGMII I/O power group[10]	NVCC_RGMII	1.15	—	2.625	V	• 1.15 V – 1.30 V in HSIC 1.2 V mode • 1.43 V – 1.58 V in RGMII 1.5 V mode • 1.70 V – 1.90 V in RGMII 1.8 V mode • 2.25 V – 2.625 V in RGMII 2.5 V mode

Table 6. Operating Ranges (continued)

Parameter Description	Symbol	Min	Typ	Max[1]	Unit	Comment[2]
GPIO supplies[10]	NVCC_CSI, NVCC_EIM0, NVCC_EIM1, NVCC_EIM2, NVCC_ENET, NVCC_GPIO, NVCC_LCD, NVCC_NANDF, NVCC_SD1, NVCC_SD2, NVCC_SD3, NVCC_JTAG	1.65	1.8, 2.8, 3.3	3.6	V	Isolation between the NVCC_EIMx and NVCC_SDx different supplies allow them to operate at different voltages within the specified range. Example: NVCC_EIM1 can operate at 1.8 V while NVCC_EIM2 operates at 3.3 V.
	NVCC_LVDS_2P5[11] NVCC_MIPI	2.25	2.5	2.75	V	—
HDMI supply voltages	HDMI_VP	0.99	1.1	1.3	V	—
	HDMI_VPH	2.25	2.5	2.75	V	—
PCIe supply voltages	PCIE_VP	1.023	1.1	1.3	V	—
	PCIE_VPH	2.325	2.5	2.75	V	—
	PCIE_VPTX	1.023	1.1	1.3	V	—
SATA Supply voltages	SATA_VP	0.99	1.1	1.3	V	—
	SATA_VPH	2.25	2.5	2.75	V	—
Junction temperature	T_J	-20	95	105	°C	See *i.MX 6Dual/6Quad Product Lifetime Usage Estimates Application Note*, AN4724, for information on product lifetime (power-on years) for this processor.

[1] Applying the maximum voltage results in maximum power consumption and heat generation. NXP recommends a voltage set point = (Vmin + the supply tolerance). This results in an optimized power/speed ratio.

[2] See the *Hardware Development Guide for i.MX 6Quad, 6Dual, 6DualLite, 6Solo Families of Applications Processors* (IMX6DQ6SDLHDG) for bypass capacitors requirements for each of the *_CAP supply outputs.

[3] For Quad core system, connect to VDD_ARM_IN. For Dual core system, may be shorted to GND together with VDD_ARM23_CAP to reduce leakage.

[4] VDD_ARM_IN and VDD_SOC_IN must be at least 125 mV higher than the LDO Output Set Point for correct voltage regulation.

[5] VDD_ARM_CAP must not exceed VDD_CACHE_CAP by more than +50 mV. VDD_CACHE_CAP must not exceed VDD_ARM_CAP by more than 200 mV.

[6] VDD_SOC_CAP and VDD_PU_CAP must be equal.

[7] In LDO enabled mode, the internal LDO output set points must be configured such that the:

VDD_ARM LDO output set point does not exceed the VDD_SOC LDO output set point by more than 100 mV.

VDD_SOC LDO output set point is equal to the VDD_PU LDO output set point.

The VDD_ARM LDO output set point can be lower than the VDD_SOC LDO output set point, however, the minimum output set points shown in this table must be maintained.

[8] In LDO bypassed mode, the external power supply must ensure that VDD_ARM_IN does not exceed VDD_SOC_IN by more than 100 mV. The VDD_ARM_IN supply voltage can be lower than the VDD_SOC_IN supply voltage. The minimum voltages shown in this table must be maintained.

[9] To set VDD_SNVS_IN voltage with respect to Charging Currents and RTC, see the *Hardware Development Guide for i.MX 6Dual, 6Quad, 6Solo, 6DualLite Families of Applications Processors* (IMX6DQ6SDLHDG).

[10] All digital I/O supplies (NVCC_xxxx) must be powered under normal conditions whether the associated I/O pins are in use or not, and associated I/O pins need to have a pull-up or pull-down resistor applied to limit any floating gate current.

[11] This supply also powers the pre-drivers of the DDR I/O pins; therefore, it must always be provided, even when LVDS is not used.

4.1.4   External Clock Sources

Each i.MX 6DualPlus/6QuadPlus processor has two external input system clocks: a low frequency (RTC_XTALI) and a high frequency (XTALI).

The RTC_XTALI is used for low-frequency functions. It supplies the clock for wake-up circuit, power-down real time clock operation, and slow system and watchdog counters. The clock input can be connected to either an external oscillator or a crystal using the internal oscillator amplifier. Additionally, there is an internal ring oscillator, that can be used instead of RTC_XTALI when accuracy is not important.

The system clock input XTALI is used to generate the main system clock. It supplies the PLLs and other peripherals. The system clock input can be connected to either an external oscillator or a crystal using the internal oscillator amplifier.

NOTE

> The internal RTC oscillator does not provide an accurate frequency and is affected by process, voltage and temperature variations. NXP strongly recommends using an external crystal as the RTC_XTALI reference. If the internal oscillator is used instead, careful consideration should be given to the timing implications on all of the SoC modules dependent on this clock.

Table 7 shows the interface frequency requirements.

Table 7. External Input Clock Frequency

Parameter Description	Symbol	Min	Typ	Max	Unit
RTC_XTALI Oscillator[1,2]	f_{ckil}	—	32.768[3]/32.0	—	kHz
XTALI Oscillator[4,2]	f_{xtal}	—	24	—	MHz

[1]   External oscillator or a crystal with internal oscillator amplifier.

[2]   The required frequency stability of this clock source is application dependent. For recommendations, see the Hardware Development Guide for i.MX 6Dual, 6Quad, 6Solo, 6DualLite Families of Applications Processors (IMX6DQ6SDLHDG).

[3]   Recommended nominal frequency 32.768 kHz.

[4]   External oscillator or a fundamental frequency crystal with internal oscillator amplifier.

The typical values shown in Table 7 are required for use with NXP BSPs to ensure precise time keeping and USB operation. For RTC_XTALI operation, two clock sources are available:

- On-chip 40 kHz ring oscillator: This clock source has the following characteristics:
  — Approximately 25 µA more Idd than crystal oscillator
  — Approximately ±50% tolerance
  — No external component required
  — Starts up quicker than 32 kHz crystal oscillator
- External crystal oscillator with on-chip support circuit

4.4.5   MLB PLL

The MediaLB PLL is necessary in the MediaLB 6-Pin implementation to phase align the internal and external clock edges, effectively tuning out the delay of the differential clock receiver and is also responsible for generating the higher speed internal clock, when the internal-to-external clock ratio is not 1:1.

Table 18. MLB PLL Electrical Parameters

Parameter	Value
Lock time	<1.5 ms

4.4.6   ARM PLL

Table 19. ARM PLL Electrical Parameters

Parameter	Value
Clock output range	650 MHz~1.3 GHz
Reference clock	24 MHz
Lock time	<2250 reference cycles

4.5   On-Chip Oscillators

4.5.1   OSC24M

This block implements an amplifier that when combined with a suitable quartz crystal and external load capacitors implements an oscillator. The oscillator is powered from NVCC_PLL_OUT.

The system crystal oscillator consists of a Pierce-type structure running off the digital supply. A straight forward biased-inverter implementation is used.

4.5.2   OSC32K

This block implements an amplifier that when combined with a suitable quartz crystal and external load capacitors implements a low power oscillator. It also implements a power mux such that it can be powered from either a ~3 V backup battery (VDD_SNVS_IN) or VDD_HIGH_IN such as the oscillator consumes power from VDD_HIGH_IN when that supply is available and transitions to the back up battery when VDD_HIGH_IN is lost.

In addition, if the clock monitor determines that the OSC32K is not present, then the source of the 32 kHz clock will automatically switch to the internal ring oscillator.

4.7.1 General Purpose I/O AC Parameters

The I/O AC parameters for GPIO in slow and fast modes are presented in the Table 28 and Table 29, respectively. Note that the fast or slow I/O behavior is determined by the appropriate control bits in the IOMUXC control registers.

Table 28. General Purpose I/O AC Parameters 1.8 V Mode

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Output Pad Transition Times, rise/fall (Max Drive, DSE=111)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate	—	—	2.72/2.79 1.51/1.54	ns
Output Pad Transition Times, rise/fall (High Drive, DSE=101)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate	—	—	3.20/3.36 1.96/2.07	
Output Pad Transition Times, rise/fall (Medium Drive, DSE=100)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate	—	—	3.64/3.88 2.27/2.53	
Output Pad Transition Times, rise/fall (Low Drive. DSE=011)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate	—	—	4.32/4.50 3.16/3.17	
Input Transition Times[1]	trm	—	—	—	25	ns

[1] Hysteresis mode is recommended for inputs with transition times greater than 25 ns.

Table 29. General Purpose I/O AC Parameters 3.3 V Mode

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Output Pad Transition Times, rise/fall (Max Drive, DSE=101)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate	—	—	1.70/1.79 1.06/1.15	ns
Output Pad Transition Times, rise/fall (High Drive, DSE=011)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate	—	—	2.35/2.43 1.74/1.77	
Output Pad Transition Times, rise/fall (Medium Drive, DSE=010)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate	—	—	3.13/3.29 2.46/2.60	
Output Pad Transition Times, rise/fall (Low Drive. DSE=001)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate	—	—	5.14/5.57 4.77/5.15	
Input Transition Times[1]	trm	—	—	—	25	ns

[1] Hysteresis mode is recommended for inputs with transition times greater than 25 ns.

Figure 14 to Figure 17 provide few examples of basic EIM accesses to external memory devices with the timing parameters mentioned previously for specific control parameters settings.
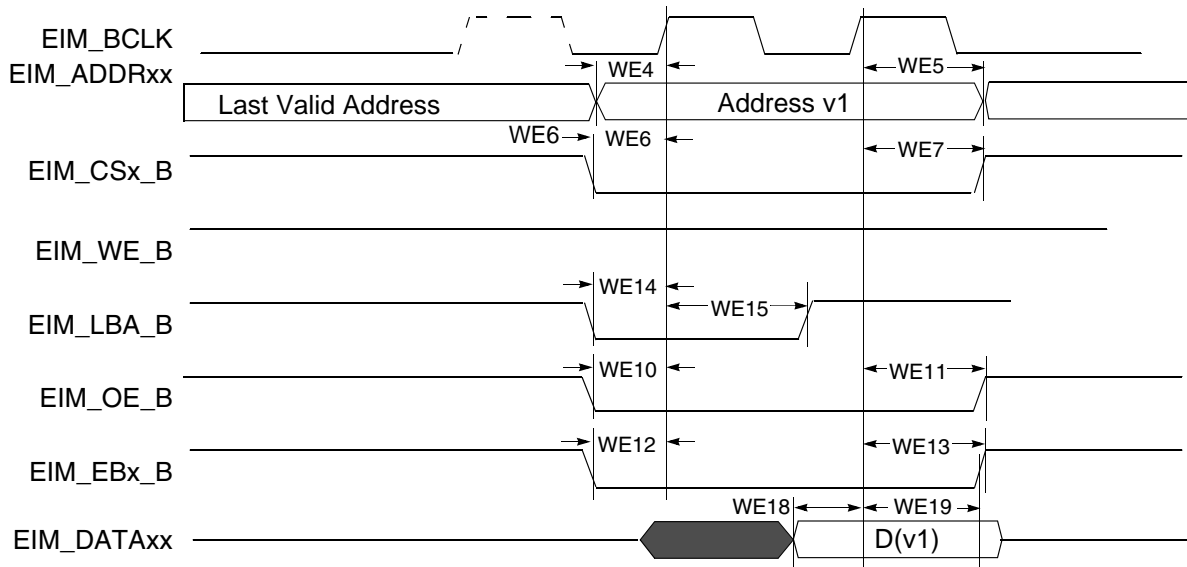

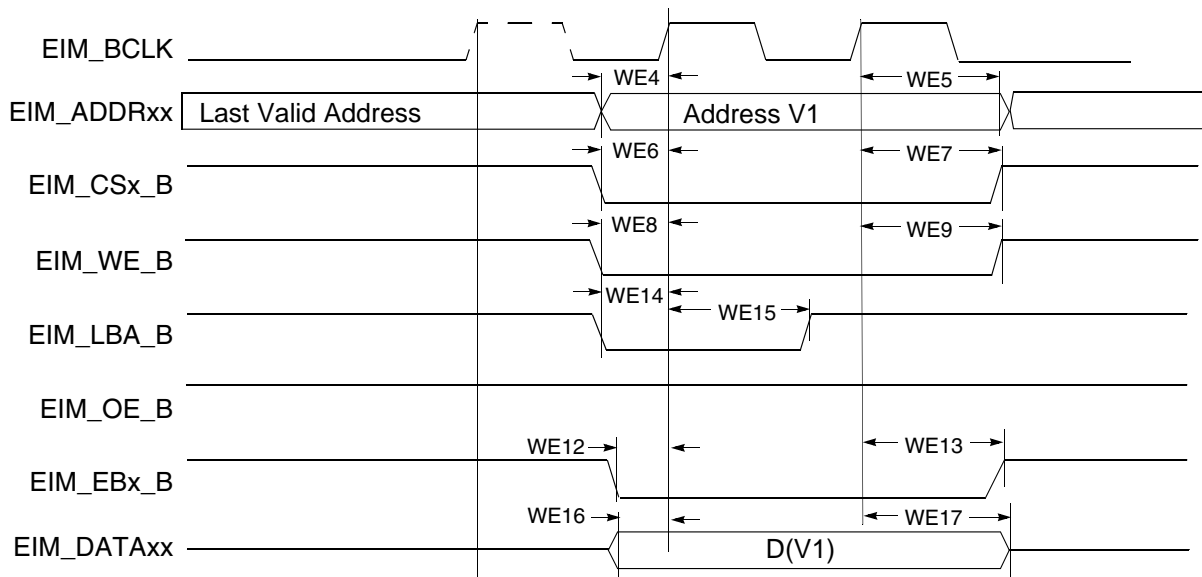**Figure 14. Synchronous Memory Read Access, WSC=1**

Figure 15. Synchronous Memory, Write Access, WSC=1, WBEA=0 and WADVN=0

4.12.3   Enhanced Serial Audio Interface (ESAI) Timing Parameters

The ESAI consists of independent transmitter and receiver sections, each section with its own clock generator. Table 49 shows the interface timing values. The number field in the table refers to timing signals found in Figure 37 and Figure 38.

Table 49. Enhanced Serial Audio Interface (ESAI) Timing

| ID	Parameter[1,2]	Symbol	Expression[2]	Min	Max	Condition[3]	Unit
62	Clock cycle[4]	t_{SSICC}	$4 \times T_C$ $4 \times T_C$	30.0 30.0	— —	i ck i ck	ns
63	Clock high period: • For internal clock • For external clock	— —	$2 \times T_C - 9.0$ $2 \times T_C$	6 15	— —	— —	ns
64	Clock low period: • For internal clock • For external clock	— —	$2 \times T_C - 9.0$ $2 \times T_C$	6 15	— —	— —	ns
65	ESAI_RX_CLK rising edge to ESAI_RX_FS out (bl) high	— —	— —	— —	19.0 7.0	x ck i ck a	ns
66	ESAI_RX_CLK rising edge to ESAI_RX_FS out (bl) low	— —	— —	— —	19.0 7.0	x ck i ck a	ns
67	ESAI_RX_CLK rising edge to ESAI_RX_FS out (wr) high[5]	— —	— —	— —	19.0 9.0	x ck i ck a	ns
68	ESAI_RX_CLK rising edge to ESAI_RX_FS out (wr) low[5]	— —	— —	— —	19.0 9.0	x ck i ck a	ns
69	ESAI_RX_CLK rising edge to ESAI_RX_FS out (wl) high	— —	— —	— —	19.0 6.0	x ck i ck a	ns
70	ESAI_RX_CLK rising edge to ESAI_RX_FSout (wl) low	— —	— —	— —	17.0 7.0	x ck i ck a	ns
71	Data in setup time before ESAI_RX_CLK (serial clock in synchronous mode) falling edge	— —	— —	12.0 19.0	— —	x ck i ck	ns
72	Data in hold time after ESAI_RX_CLK falling edge	— —	— —	3.5 9.0	— —	x ck i ck	ns
73	ESAI_RX_FS input (bl, wr) high before ESAI_RX_CLK falling edge[5]	— —	— —	2.0 19.0	— —	x ck i ck a	ns
74	ESAI_RX_FS input (wl) high before ESAI_RX_CLK falling edge	— —	— —	2.0 19.0	— —	x ck i ck a	ns
75	ESAI_RX_FS input hold time after ESAI_RX_CLK falling edge	— —	— —	2.5 8.5	— —	x ck i ck a	ns
78	ESAI_TX_CLK rising edge to ESAI_TX_FS out (bl) high	— —	— —	— —	19.0 8.0	x ck i ck	ns
79	ESAI_TX_CLK rising edge to ESAI_TX_FS out (bl) low	— —	— —	— —	20.0 10.0	x ck i ck	ns
80	ESAI_TX_CLK rising edge to ESAI_TX_FS out (wr) high[5]	— —	— —	— —	20.0 10.0	x ck i ck	ns
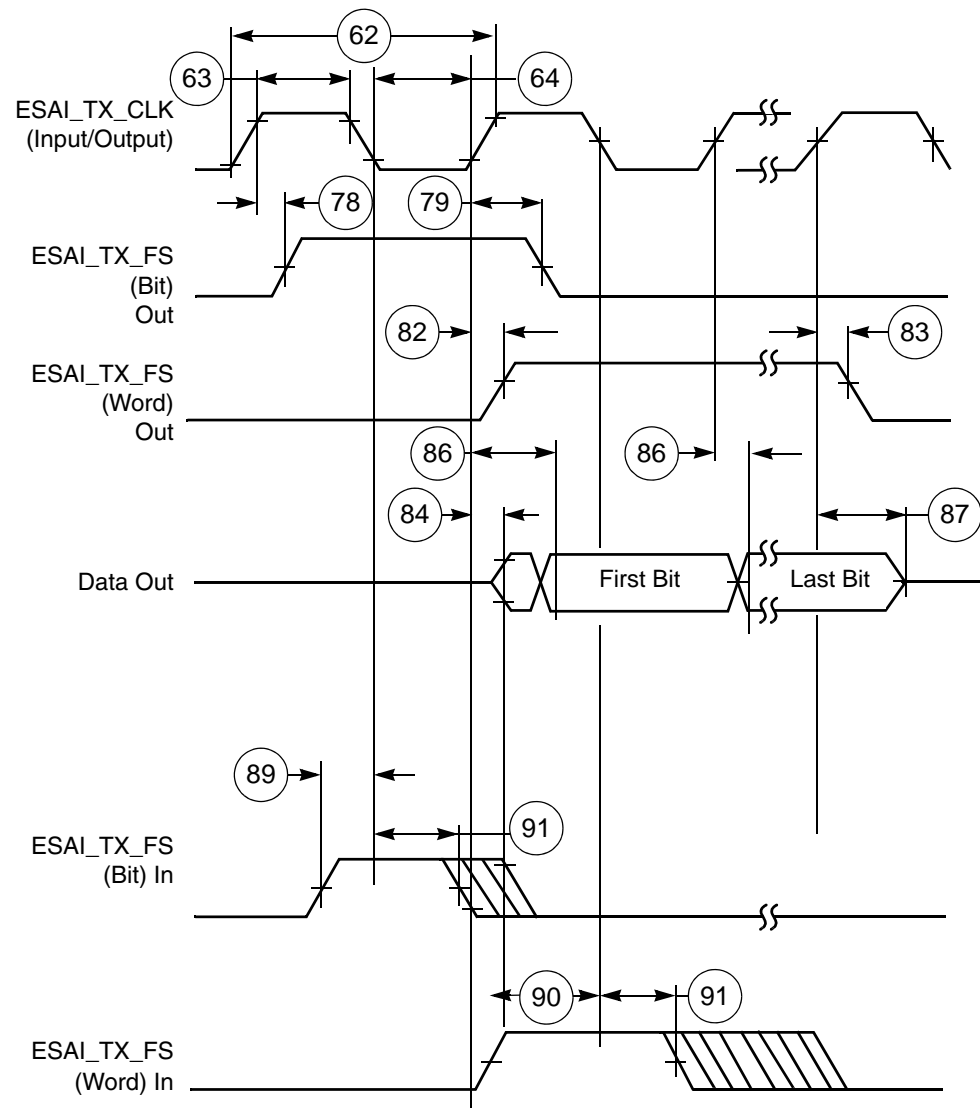
Figure 37. ESAI Transmitter Timing
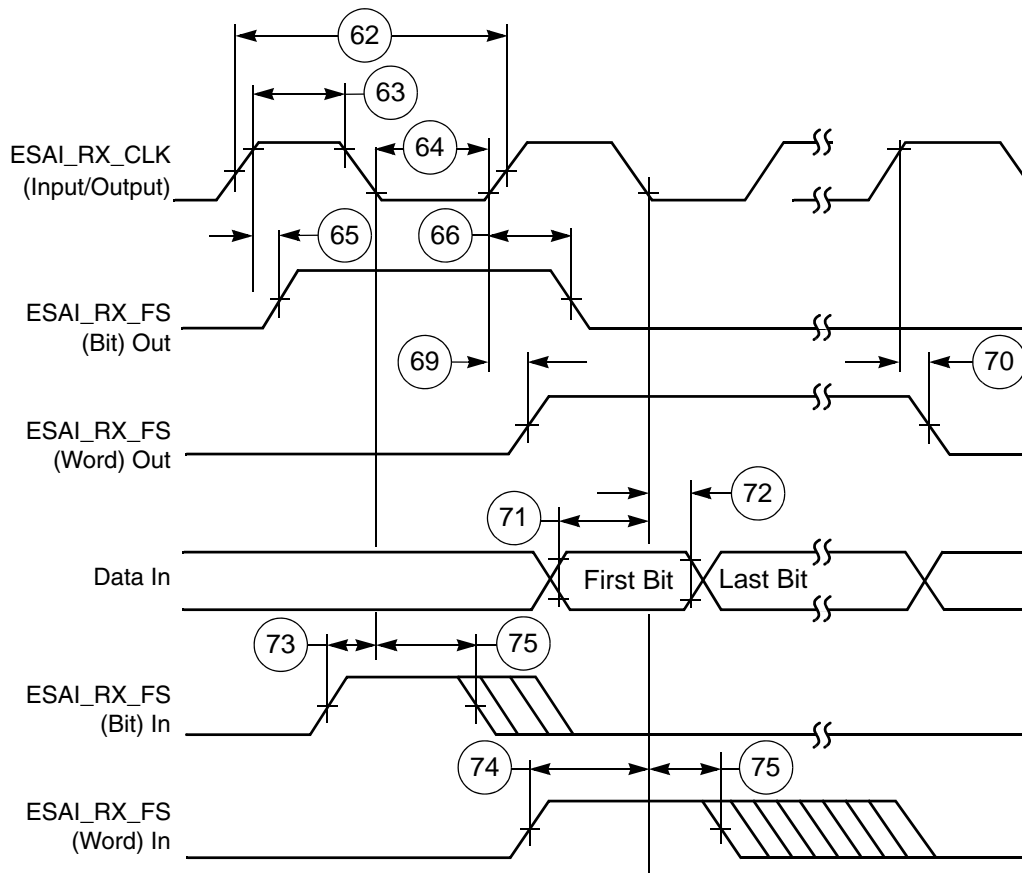
Figure 38. ESAI Receiver Timing

**Table 55. MII Asynchronous Inputs Signal Timing**

ID	Characteristic	Min	Max	Unit
M9[1]	ENET_CRS to ENET_COL minimum pulse width	1.5	—	ENET_TX_CLK period

[1] ENET_COL has the same timing in 10-Mbit 7-wire interface mode.

4.12.5.1.4   MII Serial Management Channel Timing (ENET_MDIO and ENET_MDC)

The MDC frequency is designed to be equal to or less than 2.5 MHz to be compatible with the IEEE 802.3 MII specification. However the ENET can function correctly with a maximum MDC frequency of 15 MHz.

Figure 45 shows MII asynchronous input timings. Table 56 describes the timing parameters (M10–M15) shown in the figure.
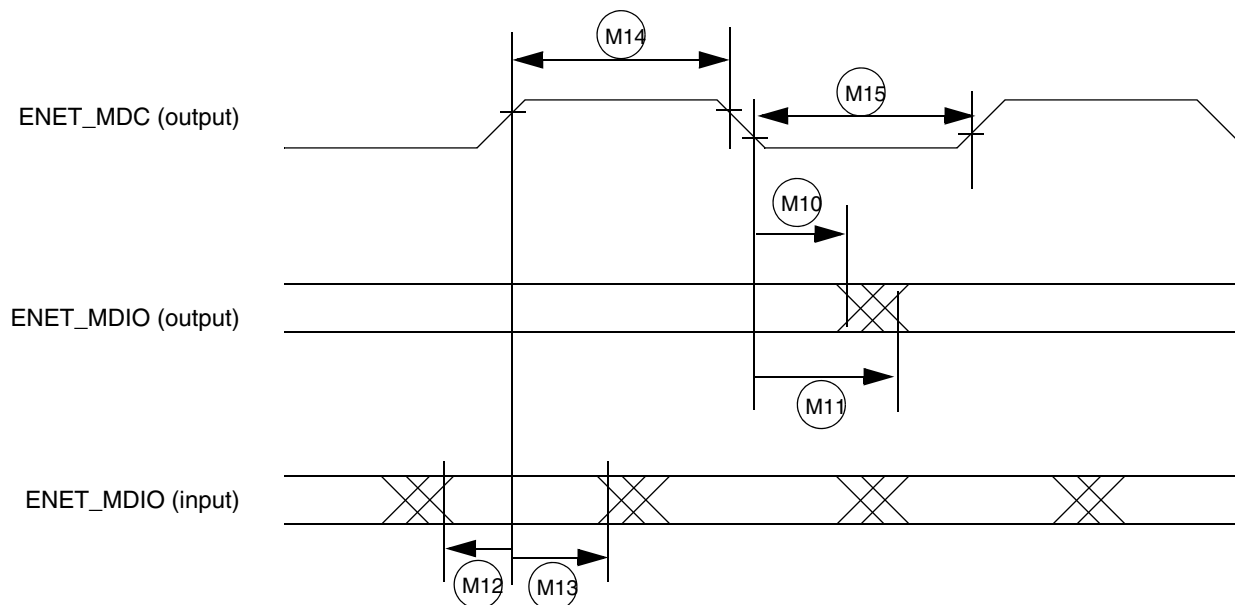
Figure 45. MII Serial Management Channel Timing Diagram

Table 56. MII Serial Management Channel Timing

ID	Characteristic	Min	Max	Unit
M10	ENET_MDC falling edge to ENET_MDIO output invalid (minimum propagation delay)	0	—	ns
M11	ENET_MDC falling edge to ENET_MDIO output valid (maximum propagation delay)	—	5	ns
M12	ENET_MDIO (input) to ENET_MDC rising edge setup	18	—	ns
M13	ENET_MDIO (input) to ENET_MDC rising edge hold	0	—	ns
M14	ENET_MDC pulse width high	40%	60%	ENET_MDC period
M15	ENET_MDC pulse width low	40%	60%	ENET_MDC period

4.12.5.2 RMII Mode Timing

In RMII mode, ENET_CLK is used as the REF_CLK, which is a 50 MHz ± 50 ppm continuous reference clock. ENET_RX_EN is used as the ENET_RX_EN in RMII. Other signals under RMII mode include ENET_TX_EN, ENET0_TXD[1:0], ENET_RXD[1:0] and ENET_RX_ER.

Figure 46 shows RMII mode timings. Table 57 describes the timing parameters (M16–M21) shown in the figure.
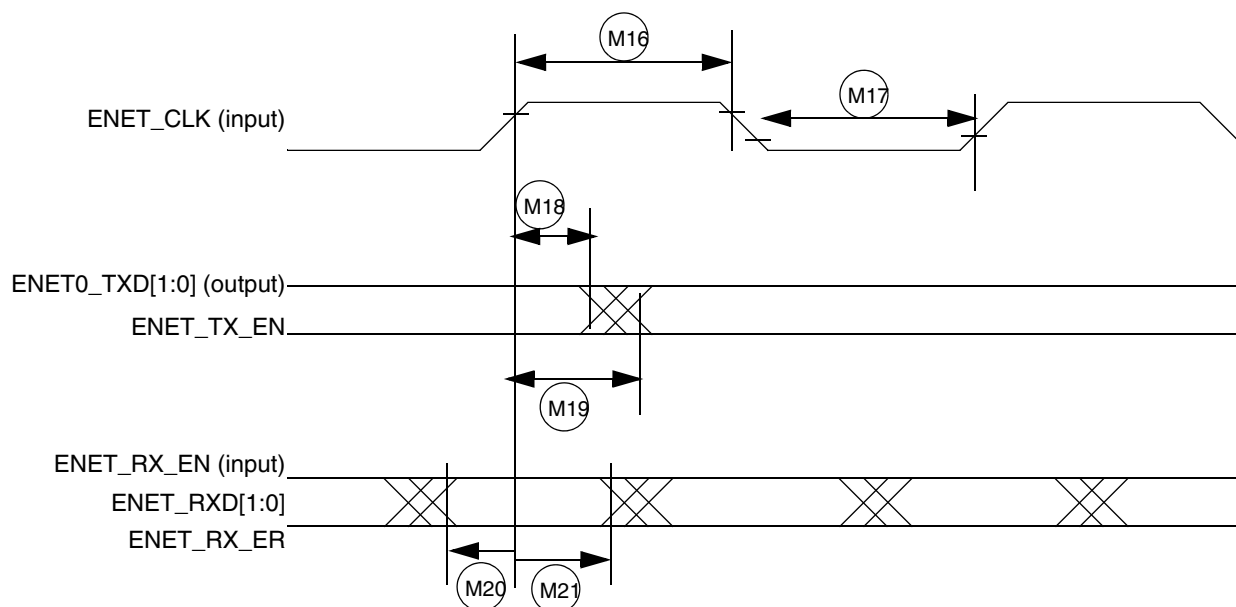

Figure 46. RMII Mode Signal Timing Diagram

Table 57. RMII Signal Timing

ID	Characteristic	Min	Max	Unit
M16	ENET_CLK pulse width high	35%	65%	ENET_CLK period
M17	ENET_CLK pulse width low	35%	65%	ENET_CLK period
M18	ENET_CLK to ENET0_TXD[1:0], ENET_TX_EN invalid	4	—	ns
M19	ENET_CLK to ENET0_TXD[1:0], ENET_TX_EN valid	—	13.5	ns
M20	ENET_RXD[1:0], ENET_RX_EN(ENET_RX_EN), ENET_RX_ER to ENET_CLK setup	4	—	ns
M21	ENET_CLK to ENET_RXD[1:0], ENET_RX_EN, ENET_RX_ER hold	2	—	ns

Power-up time for the HDMI 3D Tx PHY while operating with the fastest input reference clock supported (340 MHz) is 133 µs.

4.12.7.2   Electrical Characteristics

The table below provides electrical characteristics for the HDMI 3D Tx PHY. The following three figures illustrate various definitions and measurement conditions specified in the table below.
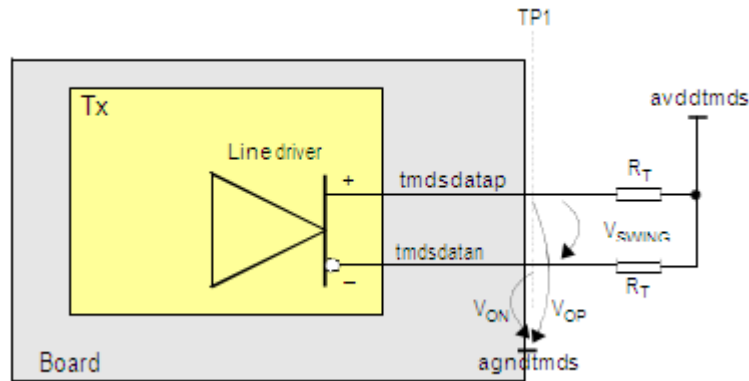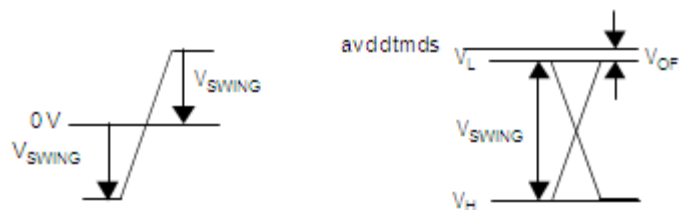

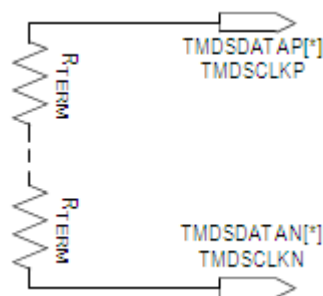**Figure 50. Driver Measuring Conditions**

Figure 51. Driver Definitions

Figure 52. Source Termination

Table 59. Electrical Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Operating conditions for HDMI						
avddtmds	Termination supply voltage	—	3.15	3.3	3.45	V

Table 59. Electrical Characteristics (continued)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
R_T	Termination resistance	—	45	50	55	Ω
TMDS drivers DC specifications						
V_{OFF}	Single-ended standby voltage	RT = 50 Ω	avddtmds ± 10 mV			mV
V_{SWING}	Single-ended output swing voltage	For measurement conditions and definitions, see the first two figures above. Compliance point TP1 as defined in the HDMI specification, version 1.3a, section 4.2.4.	400	—	600	mV
V_H	Single-ended output high voltage For definition, see the second figure above.	If attached sink supports TMDSCLK < or = 165 MHz	avddtmds ± 10 mV			mV
		If attached sink supports TMDSCLK > 165 MHz	avddtmds − 200 mV	—	avddtmds + 10 mV	mV
V_L	Single-ended output low voltage For definition, see the second figure above.	If attached sink supports TMDSCLK < or = 165 MHz	avddtmds − 600 mV	—	avddtmds − 400mV	mV
		If attached sink supports TMDSCLK > 165 MHz	avddtmds − 700 mV	—	avddtmds − 400 mV	mV
R_{TERM}	Differential source termination load (inside HDMI 3D Tx PHY) Although the HDMI 3D Tx PHY includes differential source termination, the user-defined value is set for each single line (for illustration, see the third figure above). **Note:** R_{TERM} can also be configured to be open and not present on TMDS channels.	—	50	—	200	Ω
Hot plug detect specifications						
HPD^{VH}	Hot plug detect high range	—	2.0	—	5.3	V
$VHPD_{VL}$	Hot plug detect low range	—	0	—	0.8	V
HPD_Z	Hot plug detect input impedance	—	10	—	—	kΩ
HPD_t	Hot plug detect time delay	—	—	—	100	µs

4.12.8 Switching Characteristics

Table 60 describes switching characteristics for the HDMI 3D Tx PHY. Figure 53 to Figure 57 illustrate various parameters specified in table.

NOTE

All dynamic parameters related to the TMDS line drivers' performance imply the use of assembly guidelines.

Table 65 shows timing characteristics of signals presented in Figure 63 and Figure 64.

Table 65. Synchronous Display Interface Timing Characteristics (Pixel Level)

ID	Parameter	Symbol	Value	Description	Unit
IP5	Display interface clock period	Tdicp	(see[1])	Display interface clock IPP_DISP_CLK	ns
IP6	Display pixel clock period	Tdpcp	DISP_CLK_PER_PIXEL $\times$ Tdicp	Time of translation of one pixel to display, DISP_CLK_PER_PIXEL—number of pixel components in one pixel (1.*n*). The DISP_CLK_PER_PIXEL is virtual parameter to define display pixel clock period. The DISP_CLK_PER_PIXEL is received by DC/DI one access division to *n* components.	ns
IP7	Screen width time	Tsw	(SCREEN_WIDTH) $\times$ Tdicp	SCREEN_WIDTH—screen width in, interface clocks. horizontal blanking included. The SCREEN_WIDTH should be built by suitable DI's counter[2].	ns
IP8	HSYNC width time	Thsw	(HSYNC_WIDTH)	HSYNC_WIDTH—Hsync width in DI_CLK with 0.5 DI_CLK resolution. Defined by DI's counter.	ns
IP9	Horizontal blank interval 1	Thbi1	BGXP $\times$ Tdicp	BGXP—width of a horizontal blanking before a first active data in a line (in interface clocks). The BGXP should be built by suitable DI's counter.	ns
IP10	Horizontal blank interval 2	Thbi2	(SCREEN_WIDTH – BGXP – FW) $\times$ Tdicp	Width a horizontal blanking after a last active data in a line (in interface clocks) FW—with of active line in interface clocks. The FW should be built by suitable DI's counter.	ns
IP12	Screen height	Tsh	(SCREEN_HEIGHT) $\times$ Tsw	SCREEN_HEIGHT— screen height in lines with blanking. The SCREEN_HEIGHT is a distance between 2 VSYNCs. The SCREEN_HEIGHT should be built by suitable DI's counter.	ns
IP13	VSYNC width	Tvsw	VSYNC_WIDTH	VSYNC_WIDTH—Vsync width in DI_CLK with 0.5 DI_CLK resolution. Defined by DI's counter.	ns
IP14	Vertical blank interval 1	Tvbi1	BGYP $\times$ Tsw	BGYP—width of first Vertical blanking interval in line. The BGYP should be built by suitable DI's counter.	ns
IP15	Vertical blank interval 2	Tvbi2	(SCREEN_HEIGHT – BGYP – FH) $\times$ Tsw	Width of second vertical blanking interval in line. The FH should be built by suitable DI's counter.	ns

4.12.15.1 PCIE_REXT Reference Resistor Connection

The impedance calibration process requires connection of reference resistor 200 Ω. 1% precision resistor on PCIE_REXT pads to ground. It is used for termination impedance calibration.

4.12.16 Pulse Width Modulator (PWM) Timing Parameters

This section describes the electrical information of the PWM. The PWM can be programmed to select one of three clock signals as its source frequency. The selected clock signal is passed through a prescaler before being input to the counter. The output is available at the pulse-width modulator output (PWMO) external pin.

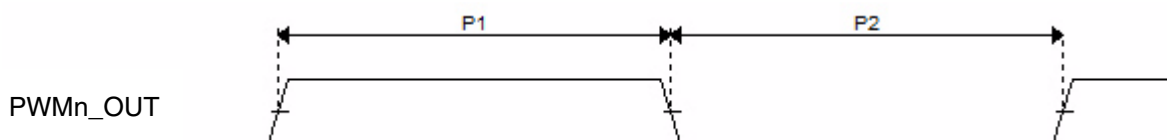Figure 83 depicts the timing of the PWM, and Table 76 lists the PWM timing parameters.

Figure 83. PWM Timing

Table 76. PWM Output Timing Parameters

ID	Parameter	Min	Max	Unit
—	PWM Module Clock Frequency	0	ipg_clk	MHz
P1	PWM output pulse width high	15	—	ns
P2	PWM output pulse width low	15	—	ns

4.12.17 SATA PHY Parameters

This section describes SATA PHY electrical specifications.

4.12.17.1 Transmitter and Receiver Characteristics

The SATA PHY meets or exceeds the electrical compliance requirements defined in the SATA specifications.

NOTE

The tables in the following sections indicate any exceptions to the SATA specification or aspects of the SATA PHY that exceed the standard, as well as provide information about parameters not defined in the standard.

The following subsections provide values obtained from a combination of simulations and silicon characterization.

Table 85. SSI Receiver Timing with External Clock

ID	Parameter	Min	Max	Unit
	External Clock Operation			
SS22	AUDx_TXC/AUDx_RXC clock period	81.4	—	ns
SS23	AUDx_TXC/AUDx_RXC clock high period	36	—	ns
SS24	AUDx_TXC/AUDx_RXC clock rise time	—	6.0	ns
SS25	AUDx_TXC/AUDx_RXC clock low period	36	—	ns
SS26	AUDx_TXC/AUDx_RXC clock fall time	—	6.0	ns
SS28	AUDx_RXC high to AUDx_TXFS (bl) high	−10	15.0	ns
SS30	AUDx_RXC high to AUDx_TXFS (bl) low	10	—	ns
SS32	AUDx_RXC high to AUDx_TXFS (wl) high	−10	15.0	ns
SS34	AUDx_RXC high to AUDx_TXFS (wl) low	10	—	ns
SS35	AUDx_TXC/AUDx_RXC External AUDx_TXFS rise time	—	6.0	ns
SS36	AUDx_TXC/AUDx_RXC External AUDx_TXFS fall time	—	6.0	ns
SS40	AUDx_RXD setup time before AUDx_RXC low	10	—	ns
SS41	AUDx_RXD hold time after AUDx_RXC low	2	—	ns

NOTE

- All the timings for the SSI are given for a non-inverted serial clock polarity (TSCKP/RSCKP = 0) and a non-inverted frame sync (TFSI/RFSI = 0). If the polarity of the clock and/or the frame sync have been inverted, all the timing remains valid by inverting the clock signal AUDx_TXC/AUDx_RXC and/or the frame sync AUDx_TXFS/AUDx_RXFS shown in the tables and in the figures.

- All timings are on Audiomux Pads when SSI is being used for data transfer.

- AUDx_TXC and AUDx_RXC refer to the Transmit and Receive sections of the SSI.

- The terms, WL and BL, refer to Word Length (WL) and Bit Length (BL).

- For internal Frame Sync operation using external clock, the frame sync timing is same as that of transmit data (for example, during AC97 mode of operation).

4.12.21.2 UART RS-232 Serial Mode Timing

The following sections describe the electrical information of the UART module in the RS-232 mode.

4.12.21.2.1 UART Transmitter

Figure 94 depicts the transmit timing of UART in the RS-232 serial mode, with 8 data bit/1 stop bit format. Table 87 lists the UART RS-232 serial mode transmit timing characteristics.
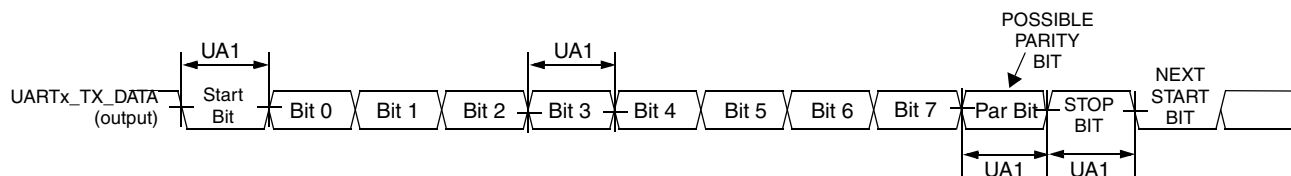

Figure 94. UART RS-232 Serial Mode Transmit Timing Diagram

Table 87. RS-232 Serial Mode Transmit Timing Parameters

ID	Parameter	Symbol	Min	Max	Unit
UA1	Transmit Bit Time	t_{Tbit}	$1/F_{baud\_rate}$[1] $- T_{ref\_clk}$[2]	$1/F_{baud\_rate} + T_{ref\_clk}$	—

[1] F_{baud_rate}: Baud rate frequency. The maximum baud rate the UART can support is (*ipg_perclk* frequency)/16.

[2] T_{ref_clk}: The period of UART reference clock *ref_clk* (*ipg_perclk* after RFDIV divider).

4.12.21.2.2 UART Receiver

Figure 95 depicts the RS-232 serial mode receive timing with 8 data bit/1 stop bit format. Table 88 lists serial mode receive timing characteristics.
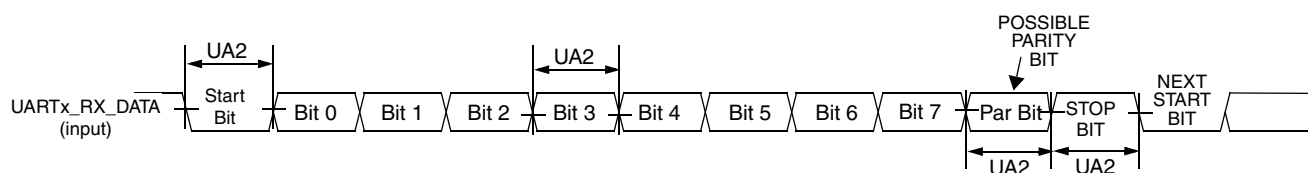

Figure 95. UART RS-232 Serial Mode Receive Timing Diagram

**Table 88. RS-232 Serial Mode Receive Timing Parameters**

ID	Parameter	Symbol	Min	Max	Unit
UA2	Receive Bit Time[1]	t_{Rbit}	$1/F_{baud\_rate}$[2] $- 1/(16 \times F_{baud\_rate})$	$1/F_{baud\_rate} + 1/(16 \times F_{baud\_rate})$	—

[1] The UART receiver can tolerate $1/(16 \times F_{baud\_rate})$ tolerance in each bit. But accumulation tolerance in one frame must not exceed $3/(16 \times F_{baud\_rate})$.

[2] F_{baud_rate}: Baud rate frequency. The maximum baud rate the UART can support is (*ipg_perclk* frequency)/16.

6.2.1.2   21 x 21 mm Non-Lidded (Bare Die) Package

Figure 103 and Figure 103 show the top, bottom, and side views of the 21×21 mm bare die package.
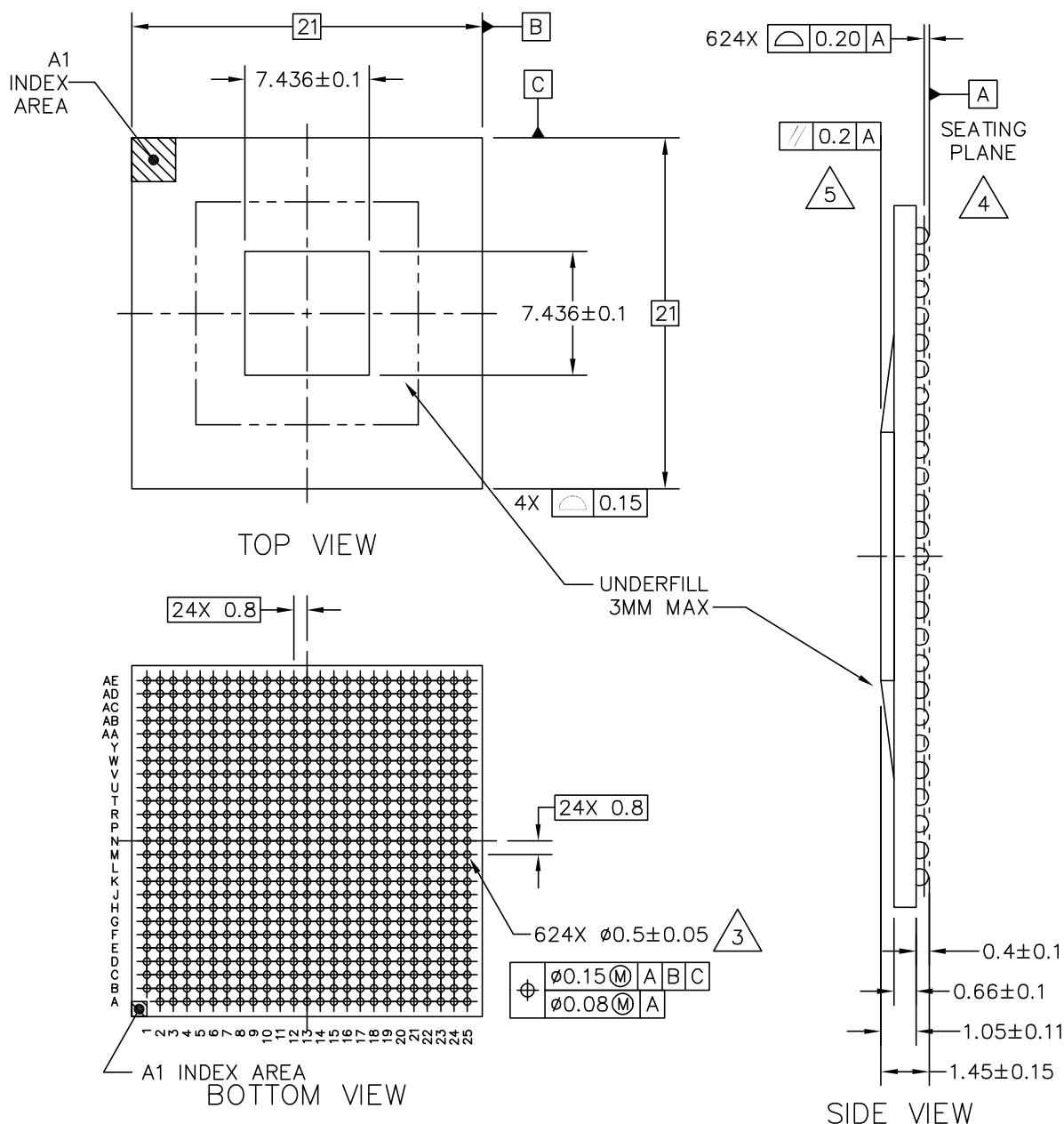
© NXP SEMICONDUCTORS N.V. ALL RIGHTS RESERVED	MECHANICAL OUTLINE	PRINT VERSION NOT TO SCALE
TITLE: 624 I/O FC PBGA, 21 X 21 PKG, 0.8 MM PITCH, NO LID	DOCUMENT NO: 98ASA00329D REV: B	
	STANDARD: JEDEC MS−034	
	SOT1642−1	07 JAN 2016

Figure 102. 21 x 21 mm Bare Die Package Top, Bottom, and Side Views (Sheet 1 of 2)

Table 95. 21 x 21 mm Supplies Contact Assignment (continued)

Supply Rail Name	Ball(s) Position(s)	Remark
VDDHIGH_CAP	H10, J10	Secondary supply for the 2.5 V domain (internal regulator output—requires capacitor if internal regulator is used)
VDDHIGH_IN	H9, J9	Primary supply for the 2.5 V regulator
VDDPU_CAP	H17, J17, K17, L17, M17, N17, P17	Secondary supply for the VPU and GPU (internal regulator output—requires capacitor if internal regulator is used)
VDDSOC_CAP	R10, T10, T13, T14, U10, U13, U14	Secondary supply for the SoC and PU (internal regulator output—requires capacitor if internal regulator is used)
VDDSOC_IN	H16, J16, K16, L16, M16, N16, P16, R16, T16, U16	Primary supply for the SoC and PU regulators
VDDUSB_CAP	F9	Secondary supply for the 3 V domain (internal regulator output—requires capacitor if internal regulator is used)
ZQPAD	AE17	Connect ZQPAD to an external 240Ω 1% resistor to GND. This is a reference used during DRAM output buffer driver calibration.

6.2.3 21 x 21 mm Functional Contact Assignments

Table 96 displays an alpha-sorted list of the signal assignments including power rails. The table also includes out of reset pad state.

Table 96. 21 x 21 mm Functional Contact Assignments

Ball Name	Ball	Power Group	Ball Type	Out of Reset Condition[1]			
				Default Mode (Reset Mode)	Default Function (Signal Name)	Input/Output	Value[2]
BOOT_MODE0	C12	VDD_SNVS_IN	GPIO	ALT0	SRC_BOOT_MODE0	Input	PD (100K)
BOOT_MODE1	F12	VDD_SNVS_IN	GPIO	ALT0	SRC_BOOT_MODE1	Input	PD (100K)
CLK1_N	C7	VDD_HIGH_CAP	—	—	CLK1_N	—	—
CLK1_P	D7	VDD_HIGH_CAP	—	—	CLK1_P	—	—
CLK2_N	C5	VDD_HIGH_CAP	—	—	CLK2_N	—	—
CLK2_P	D5	VDD_HIGH_CAP	—	—	CLK2_P	—	—
CSI_CLK0M	F4	NVCC_MIPI	—	—	CSI_CLK_N	—	—
CSI_CLK0P	F3	NVCC_MIPI	—	—	CSI_CLK_P	—	—
CSI_D0M	E4	NVCC_MIPI	—	—	CSI_DATA0_N	—	—
CSI_D0P	E3	NVCC_MIPI	—	—	CSI_DATA0_P	—	—
CSI_D1M	D1	NVCC_MIPI	—	—	CSI_DATA1_N	—	—